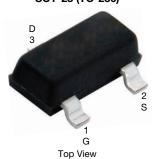


Vishay Siliconix

Automotive P-Channel 40 V (D-S) 175 °C MOSFET

SOT-23 (TO-236)



Marking Code: 9UYXX

PRODUCT SUMMARY				
V _{DS} (V)	-40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.094			
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5 \text{ V}$	0.188			
I _D (A)	-4.1			
Configuration	Single			

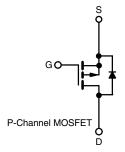
FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % Rg and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



ORDERING INFORMATION	
Package	SOT-23
Lead (Pb)-free and halogen-free	SQ2389CES (for detailed order number please see www.vishay.com/doc?79771)

ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unless	otherwise noted	d)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	-40	M
Gate-source voltage		V _{GS}	± 20	V
Continuous drain current	T _C = 25 °C		-4.1	
	T _C = 125 °C	- I _D	-2.4	
Continuous source current (diode conduction)		I _S	-3.6	Α
Pulsed drain current ^a		I _{DM}	-16	
Single pulse avalanche current	1 0.1 ml l	I _{AS}	-12	
Single pulse avalanche energy	L = 0.1 mH	E _{AS}	7.2	mJ
Maximum power dissipation	T _C = 25 °C	D	3	W
	T _C = 125 °C	P_{D}	1	VV
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount b	R_{thJA}	166	°C/W
Junction-to-foot (drain)		R _{thJF}	50	G/VV

Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %
- b. When mounted on 1" square PCB (FR4 material)



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							L
Drain-source breakdown voltage	V _{DS}	V _{GS} =	0 V, I _D = -250 μA	-40	-	-	.,
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = -250 μA	-1.5	-2.0	-2.5	V
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA
		V _{GS} = 0 V	V _{DS} = -40 V	-	-	-1	
Zero gate voltage drain current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -40 V, T _J = 125 °C	-	_	-50	μA
		V _{GS} = 0 V	V _{DS} = -40 V, T _J = 175 °C	-	-	-150	·
On-state drain current ^a	I _{D(on)}	V _{GS} = -10 V	V _{DS} ≤ -5 V	-10	-	-	Α
	5(0.1)	V _{GS} = -10 V	I _D = -3 A	-	0.084	0.094	
		V _{GS} = -10 V	I _D = -3 A, T _J = 125 °C	-	-	0.144	
Drain-source on-state resistance a	R _{DS(on)}	V _{GS} = -10 V	I _D = -3 A, T _J = 175 °C	-	-	0.169	V nA μA A S pF nC Ω ns
		V _{GS} = -4.5 V	I _D = -3 A	-	0.140	0.188	
Forward transconductance b	9 _{fs}		= -10 V, I _D = -3 A	-	5	-	S
Dynamic ^b	0.5		_				
Input capacitance	C _{iss}			-	414	455	
Output capacitance	Coss	V _{GS} = 0 V	V _{DS} = -20 V, f = 1 MHz	-	80	100	pF
Reverse transfer capacitance	C _{rss}			-	42	54	
Total gate charge ^c	Qg			-	8.2	12	
Gate-source charge ^c	Q _{gs}	V _{GS} = -10 V	$V_{DS} = -20 \text{ V}, I_{D} = -3 \text{ A}$	-	1.1	-	nC
Gate-drain charge ^c	Q _{gd}			-	3.0	-	
Gate resistance	R_g		f = 1 MHz	3.1	4.1	7	Ω
Turn-on delay time ^c	t _{d(on)}			-	7	10	
Rise time ^c	t _r	Von -	-20 V, R_L = 6.7 Ω	-	12	16	
Turn-off delay time ^c	t _{d(off)}	$I_D \cong -3 \text{ A, } V_{GEN} = -10 \text{ V, } R_g = 1 \Omega$		_	16	20	ns
Fall time ^c	t _f			-	4	8	
Source-Drain Diode Ratings and Charac	teristics ^b						
Pulsed current ^a	I _{SM}			-	-	-10	Α
Forward voltage	V_{SD}	l _F = ·	-1.5 A, V _{GS} = 0 V	-	-0.8	-1.2	V
Body diode reverse recovery time	t _{rr}			_	17	34	ns
Body diode reverse recovery charge	Q _{rr}		A di/dt = 100 A/va	-	14	28	nC
Reverse recovery fall time	ta	I _F = -2	A, di/dt = 100 A/μs	-	14	-	ne
Reverse recovery rise time	t _b				3	-	115
Body diode peak reverse recovery current	I _{RM(REC)}			-	-1.99	-	Α

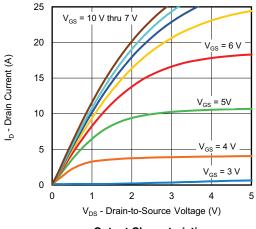
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

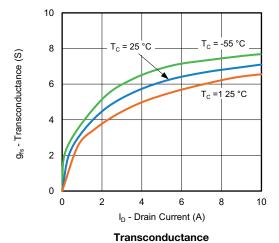
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

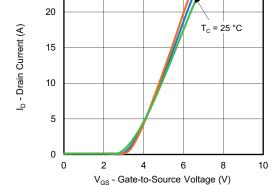


TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Output Characteristics

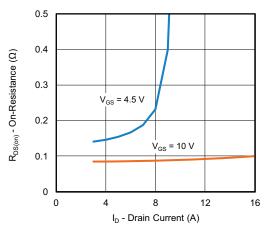




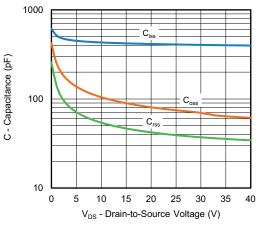
T_C = 125 °C

25

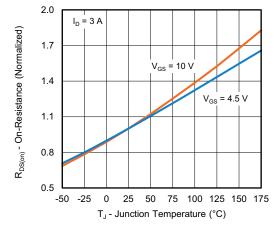
Transfer Characteristics



On-Resistance vs. Drain Current



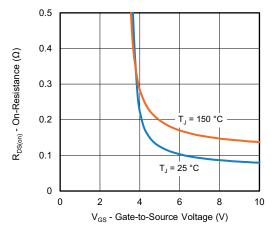
Capacitance



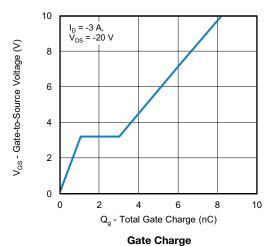
On-Resistance vs. Junction Temperature



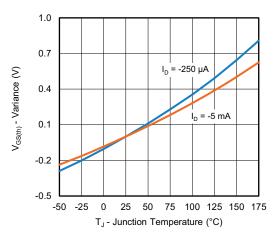
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



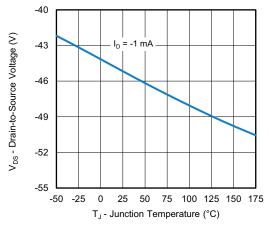
On-Resistance vs. Gate-Source Voltage



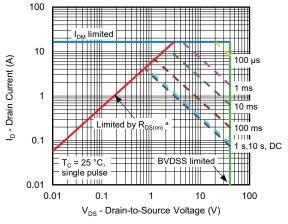
Source-Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



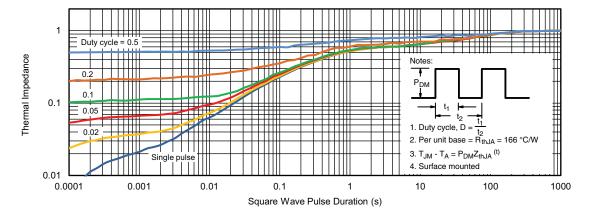
Safe Operating Area

Note

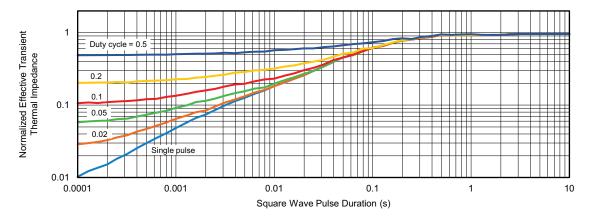
a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Notes

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62212.



SOT-23 (TO-236): 3-LEAD







Dim —	MILLIN	METERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.074	8 Ref	
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025	i Ref	
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	

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RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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